•	Application No.	Applicant(s)
Notice of Allowability	09/511,912 Examiner	NISHINAGA, TATAU Art Unit
	Felisa C. Hiteshew	1722 _′
The MAILING DATE of this communication apperature All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this apport or other appropriate communication GHTS. This application is subject to	plication. If not included will be mailed in due course. THIS
1. \boxtimes This communication is responsive to <u>the amendment filed</u> of	on December 18, 2006.	
2. The allowed claim(s) is/are <u>1-6,11,12; 14-18 and 20-23</u> .		
3.	been received. been received in Application No cuments have been received in this of this communication to file a reply ENT of this application. itted. Note the attached EXAMINER' as reason(s) why the oath or declara t be submitted. on's Patent Drawing Review (PTO- as Amendment / Comment or in the O and Amendm	complying with the requirements 'S AMENDMENT or NOTICE OF tion is deficient. 948) attached Office action of the back) of the complying with the front (not the back) of the complex
Attachment(s) 1. Notice of References Cited (PTO-892) 2. Notice of Draftperson's Patent Drawing Review (PTO-948) 3. Information Disclosure Statements (PTO/SB/08),	5. ☐ Notice of Informal Pa 6. ☐ Interview Summary Paper No./Mail Date 7. ☐ Examiner's Amendm 8. ☑ Examiner's Stateme 9. ☐ Other	(PTO-413),

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Allowable Subject Matter

- 1. Claims 1-6,11,12; 14-18 and 20-23 are allowed.
- 2. The following is an examiner's statement of reasons for allowance: The most relevant prior art of reference were those cited in previous office actions. However, they do not teach nor fairly suggest singularly or in any combination thereof a method for forming a single crystalline film comprising: forming an amorphous film on a single crystalline substrate, forming an opening in the amorphous film and thereby exposing a part of a surface of the substrate through the opening, and directing an atomic beam, a molecular beam, or a chemical beam toward the substrate at an incident angle of not more than 40 degrees with respect to the substrate surface to selectively and epitaxially grow a single crystalline film on the exposed surface of the substrate that laterally overgrows the amorphous film.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Felisa Hiteshew whose telephone number is (571) 272-1463. The examiner can normally be reached on Mondays through Thursday from 5:30 AM to 3:00 PM, off first Friday and 5:30 AM. –2 PM on second Friday.

If attempts to reach the examiner by telephone are unsuccessful, the

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examiner's supervisor, Yogendra Gupta can be reached on (571) 272-1316. The fax phone number for the organization where this application or proceeding is assigned is (571) 273-1463.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system. see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866- 217-9197 (toll-free).

FÉLISA HITESHEW PRIMARY EXAMINER